In the Claims:

 (currently amended) A method for forming ultra shallow junctions, comprising:

providing a semiconductor;

implanting a dopant species into said semiconductor; and

annealing said implanted semiconductor with an ultra high temperature anneal comprising annealing temperatures from 1150° about 1050° C to about 1350° C for a period of from about 0.5 milliseconds to about 3 milliseconds.

- 2. (previously presented) The method of claim 1 further comprising an amorphizing implant.
- 3. (previously presented) The method of claim 2 wherein said amorphizing implant comprises implanting a species from the group consisting of silicon, germanium, antimony, indium, arsenic, neon, argon, krypton, and xenon.
 - 4-18 (canceled)
- 19. (new) The method of claim 1 wherein said annealing temperature is in the range of from about 1150°C to about 1350°C.